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(54) **ORGANIC LIGHT EMITTING DISPLAY
DEVICE WITH OPAQUE ELECTRODES**

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H05B 33/06 (2006.01)

(52) **U.S. Cl.** **313/503**; 313/500; 313/504; 313/506;
313/512; 257/79; 257/88; 257/89; 428/690

(58) **Field of Classification Search** 313/504,
313/506

See application file for complete search history.

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(57) **ABSTRACT**

An organic light emitting display device is disclosed. One embodiment of the organic light emitting display device includes a substrate member in which a plurality of pixel regions are arranged, and a plurality of thin film transistors which are formed on the pixels regions, respectively. The device also includes a data line which is arranged along one side edge of each of the pixel region and a common power source line which is arranged along the other side edge of each of the plurality of pixel regions and is substantially parallel to the data line. The device further includes a first pixel electrode which is electrically connected to one of the plurality of thin film transistors and is formed in each region of the pixel regions. The device also includes an organic film which is formed on the first pixel electrode, and a second pixel electrode which is formed on the organic film. One side edge of the first pixel electrode which is close to the data line is overlapped with the data line.

14 Claims, 3 Drawing Sheets

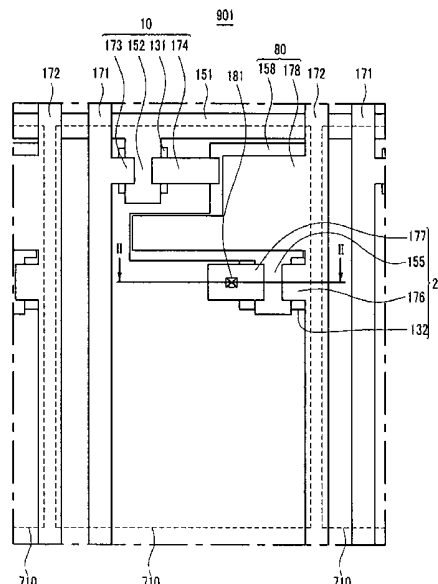


FIG. 1

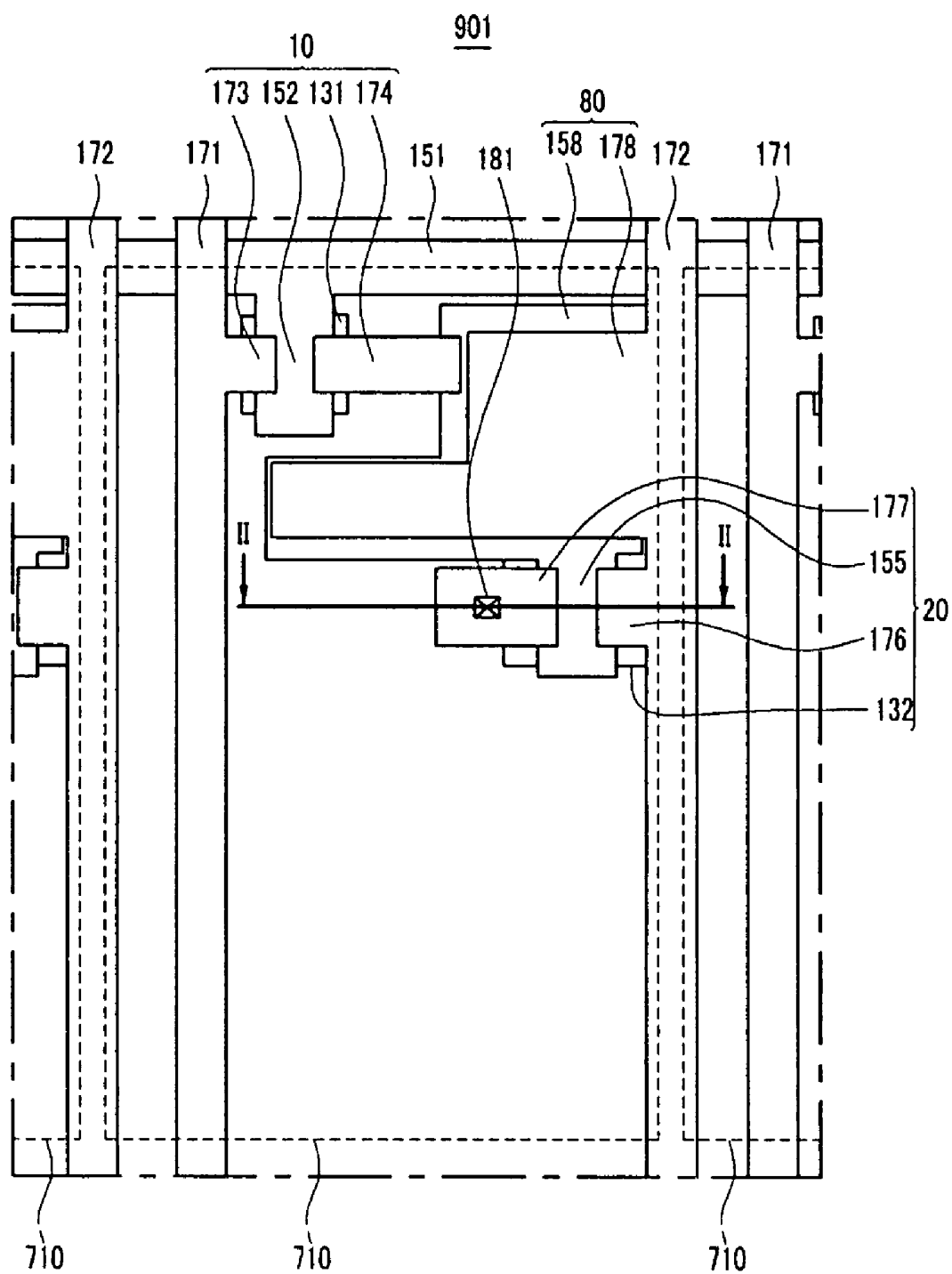


FIG. 2

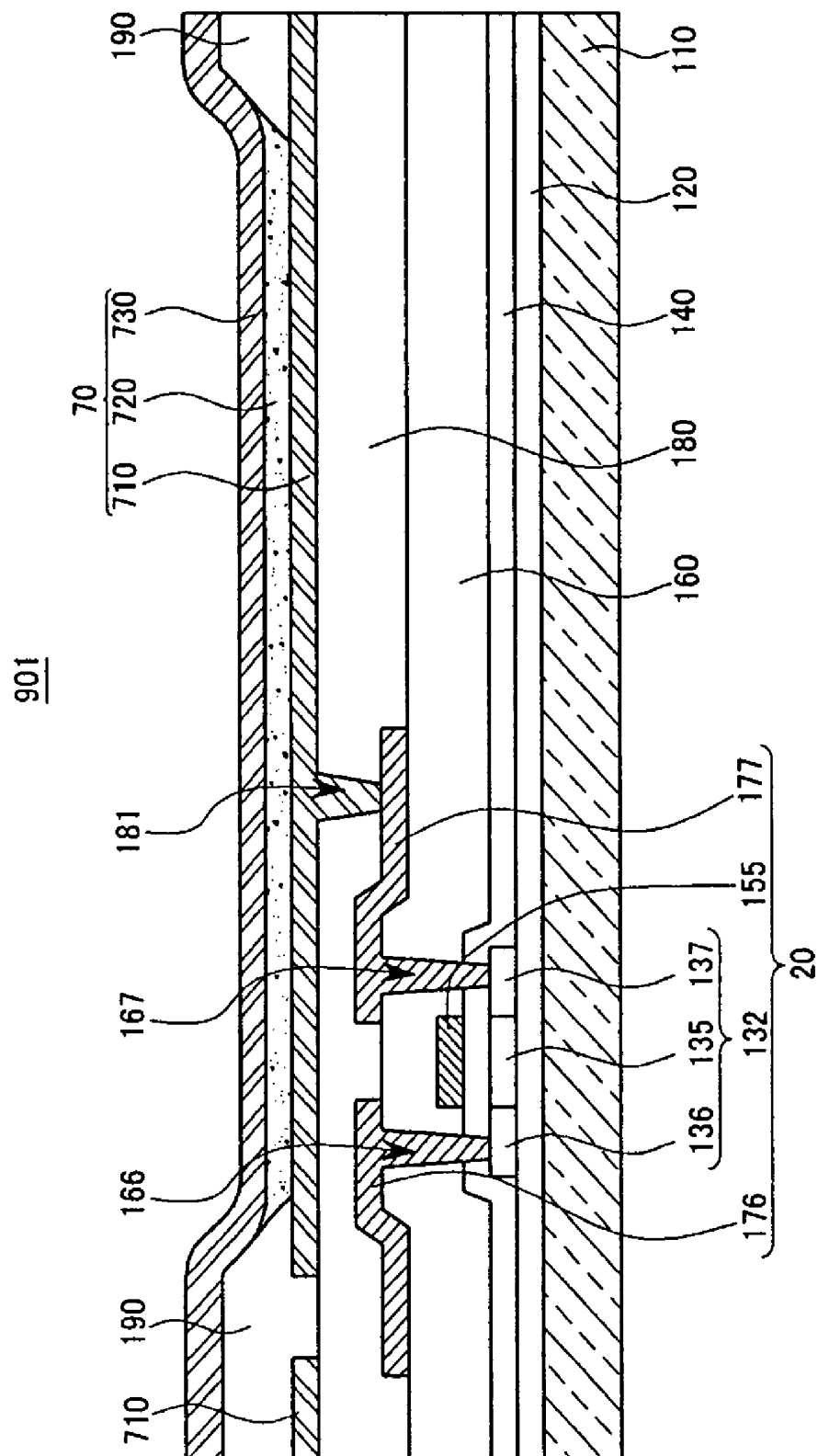
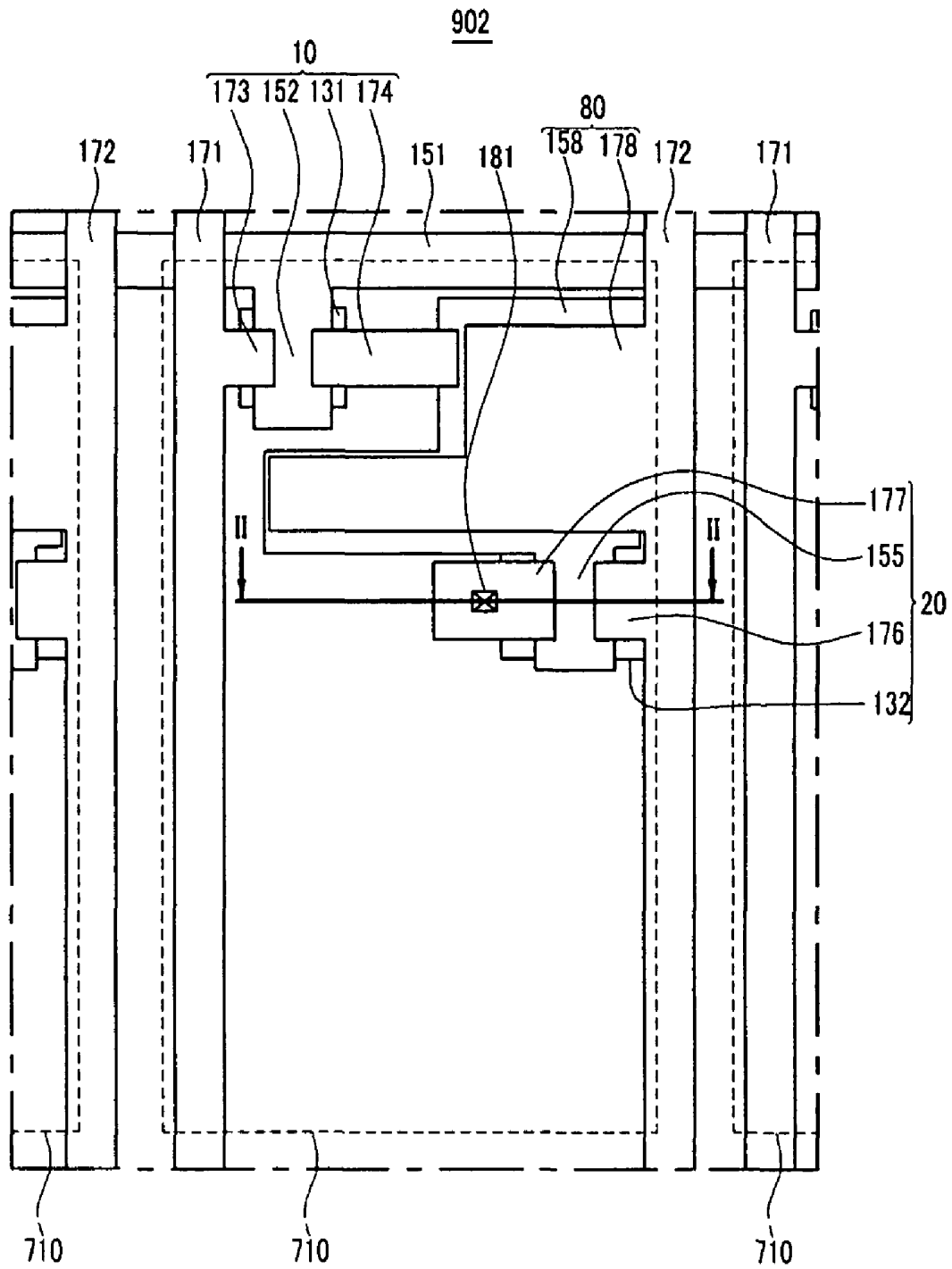


FIG. 3



ORGANIC LIGHT EMITTING DISPLAY DEVICE WITH OPAQUE ELECTRODES

CROSS-REFERENCE TO RELATED APPLICATIONS

This application claims priority to and the benefit of Korean Patent Application No. 10-2006-0111153 filed in the Korean Intellectual Property Office on Nov. 10, 2006, the entire disclosure of which is incorporated herein by reference.

BACKGROUND

1. Field

The present disclosure relates to an organic light emitting display device, and more particularly, to an organic light emitting display device having thin film transistors with improved driving characteristics.

2. Description of the Related Technology

Recently, flat panel displays have been spotlighted as next generation display devices. A plasma display panel (PDP), a liquid crystal display (LCD), an organic light emitting display device are representative examples of the flat panel displays.

An organic light emitting display device is a self-luminescent device, which displays an image by using a light-emitting organic compound. The organic light emitting display device can provide a viewing angle wider than those of other flat panel displays and implement a high resolution display. Organic light emitting display devices can be classified into an active matrix (AM) type and a passive matrix (PM) type based on the driving method. In addition, organic light emitting display devices can be classified into a top emission type, a bottom emission type, and a dual emission type based on the direction of light emission.

A pixel is a basic unit for displaying an image. Generally, in an AM type organic light emitting display device, a pixel generally includes an organic light emitting diode which emits light and a circuit unit which drives the organic light emitting diode.

Generally, the circuit unit includes two or more thin film transistors (TFTs) and one capacitor. One of the two TFTs serves as a switching element which selects an organic light emitting diode of a pixel among a plurality of pixels which needs to emit light. The other TFT serves as a driving circuit which applies a driving power source to the selected organic light emitting diode to emit light.

The organic light emitting diode includes an anode electrode from which holes are injected, a cathode electrode from which electrons are injected, and an organic film interposed between the anode and cathode electrodes.

In the organic light emitting display device described above, light emitting from the organic light emitting diode may reach the channel regions of the TFTs. When the light reaches the channel regions of the TFTs, a photo leakage current may occur, thereby deteriorating the driving characteristics of the TFTs.

SUMMARY OF CERTAIN INVENTIVE ASPECTS

One aspect of the invention provides an organic light emitting display device capable of blocking light from reaching channel regions of TFTs to prevent generation of a photo leakage current and deterioration of driving characteristics of the TFTs.

Another aspect of the invention provides an organic light emitting display device comprising: an array of pixels formed over a substrate, each of the pixels comprising an organic

light emitting diode (OLED), the OLED comprising a first pixel electrode, a second pixel electrode overlying the first pixel electrode, and an organic light emitting layer interposed between the first and second pixel electrodes, the first electrode comprising a layer formed of a substantially opaque material; and at least one thin film transistor (TFT) interposed between the substrate and one of the pixels; and wherein the first pixel electrode of the one pixel is configured to substantially block light emitting from the organic light emitting layer from reaching the thin film transistor.

The first pixel electrode may be configured to sufficiently block the light from reaching the TFT such that substantially no photo leakage current occurs at the TFT. The first pixel electrode may at least partially overlie the TFT. The TFT may comprise a semiconductor layer including a channel region, and the first pixel electrode may overlie substantially the entire portion of the channel region. The first pixel electrode may overlie substantially the entire portion of the TFT.

The first pixel electrode may have a first edge portion, and the device may further comprise a data line extending along the first edge portion while at least partially overlapping with the first edge portion in a direction substantially perpendicular to the substrate. The data line may be electrically connected to the TFT. The first pixel electrode may substantially overlie the data line. The first pixel electrode may have a second edge portion on the opposite side from the first edge portion, and the device may further comprise a common power source line extending along the second edge portion while at least partially overlapping with the second edge portion in a direction substantially perpendicular to the substrate.

The common power source line may be electrically connected to the TFT. The TFT may be positioned under the first pixel electrode between the first and second edge portions thereof, and the first pixel electrode may overlie substantially the entire portion of the TFT. The device may further comprise another common power source line extending adjacent to and substantially parallel to the data line while at least partially overlapping with the first edge portion in a direction substantially perpendicular to the substrate.

The substantially opaque material may be silver (Ag) or a silver alloy. The first electrode may further comprise a layer formed of a substantially transparent material. The substantially transparent material may be indium tin oxide (ITO). The first electrode may have an ITO/Ag/ITO layer structure.

Another aspect of the invention provides an organic light emitting display device comprising: a plurality of data lines formed over a substrate, the data lines extending substantially parallel to one another; and a plurality of power lines formed over the substrate, the power lines extending substantially parallel to one another and to the data lines, the power lines alternating with the data lines; and an array of organic light emitting diodes (OLEDs), each of the OLEDs comprising a first pixel electrode, a second pixel electrode overlying the first pixel electrode, and an organic light emitting layer interposed between the first and second pixel electrodes, the first electrode comprising a layer formed of a substantially opaque material, at least one of the first pixel electrodes having a first edge portion and a second edge portion on the opposite side from the first edge portion, the first and second edge portions extending substantially parallel to the data lines, wherein the first edge portion at least partially overlaps with one of the data lines, and wherein the second edge portion at least partially overlaps with one of the power lines, the one power line being second closest to the one data line.

The first edge portion may further overlap with another of the power lines, the other power line being closest to the one

data line. The device may further comprise at least one thin film transistor formed over the substrate and under the at least one first pixel electrode. The at least one first pixel electrode may be configured to substantially block light emitting from the organic light emitting layer from reaching the thin film transistor.

Another aspect of the invention provides an organic light emitting display device including a substrate member in which a plurality of pixel regions are arranged; a plurality of thin film transistors which are formed on the pixels regions, respectively; a data line which is arranged along one side edge of each of the plurality of pixel region; a common power source line which is arranged along the other side edge of each of the plurality of pixel regions and is substantially parallel to the data line; a first pixel electrode which is electrically connected to one of the thin film transistors and formed in each region of the plurality of pixel regions; an organic film which is formed on the first pixel electrode; and a second pixel electrode which is formed on the organic film. One side edge of the first pixel electrode which is close to the data line is overlapped with the data line.

The one side edge of the first pixel electrode which overlaps with the data line may be formed to cross the data line. The other side edge of the first pixel electrode which is close to the common power source line and faces the one side may be overlapped with the common power source line. An end of the one side edge of the first pixel electrode which is formed to cross the data line may be overlapped with the common power source line of an adjacent pixel region. In addition, the first pixel electrode may be overlapped with the thin film transistors. In addition, the first pixel electrode may be made of materials including conductive reflective materials, and the second pixel electrode may be made of materials including conductive transparent materials. Accordingly, the deterioration of driving characteristics of the TFTs can be prevented.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a top plan view illustrating an organic light emitting display device according to one embodiment;

FIG. 2 is a cross-sectional view taken along the line II-II of FIG. 1; and

FIG. 3 is a top plan view illustrating an organic light emitting display device according to another embodiment.

DETAILED DESCRIPTION OF CERTAIN INVENTIVE EMBODIMENTS

Hereinafter, exemplary embodiments will be described in detail with reference to the attached drawings. The invention may be embodied and modified in a variety of forms, and they are not intended to limit the invention.

In the attached drawings, an organic light emitting display device including PMOS thin film transistors (TFTs) is illustrated. However, the present disclosure is not limited thereto and may be applied to NMOS or CMOS TFTs.

In addition, in the attached drawings, although active matrix (AM) type organic light emitting display devices having 2TR-1Cap structures, each of which includes two TFTs and one capacitor for one pixel are illustrated, the present disclosure is not limited thereto. Accordingly, the organic light emitting display device may include three or more TFTs and two or more capacitors in one pixel. The organic light emitting display device may have various structures with additional wirings.

In the drawings, like reference numerals indicate identical or functionally similar elements throughout the specification.

In the drawings, the thickness of layers, films, panels, regions, etc. may be exaggerated for clarity. It will be understood that when an element such as a layer, film, region or substrate is referred to as being "on" another element, it can be directly on the other element or intervening elements may also be present. In contrast, when an element is referred to as being "directly on" another element, there are no intervening elements present.

FIG. 1 is a schematic diagram illustrating a pixel of an organic light emitting display device having a plurality of pixels according to a first exemplary embodiment. FIG. 2 is a cross-sectional view taken along the line II-II of FIG. 1.

As illustrated in FIG. 1, the organic light emitting display device 901 includes a first TFT 10, a second TFT 20, a capacitor 80, and an organic light emitting diode (OLED) 70. In addition, the organic light emitting display device 901 further includes a gate line 151 extending along one direction, a data line 171 crossing the gate line 151 while being insulated therefrom, and a common power source line 172. Here, a region defined by the gate, data, and common power source lines 151, 171, and 172 may form one pixel region. However, the region defined by the gate, data, and common power source lines 151, 171, and 172 does not necessarily form a pixel region. There may be various configurations of pixel regions, based on an operating method of the organic light emitting display device 901, that is, whether the organic light emitting display device 901 is a top emission type or a bottom emission type. In addition, the pixel region may be changed based on the structure of a circuit unit including the first TFT 10, the second TFT 20, and the capacitor 80. In the embodiment described above, a region where a first pixel electrode 710 (denoted by a dotted line) is positioned can be defined as a pixel region.

In the illustrated embodiment, the data line 171 extends along one side edge of one pixel region. The common power source line 172 may extend along the other side edge of the pixel region. The common power source line 172 may run substantially parallel to the data line 171. The illustrated common power source line 172 overlaps partly with one pixel region and partly with another neighboring pixel region. In other words, the data line 171 and the common power source line 172 are positioned along two opposing edges of one pixel region.

The OLED 70 (FIG. 2) includes an anode electrode from which holes are injected, a cathode electrode from which electrons are injected, and an organic film interposed between the anode and cathode electrodes. The holes and electrons are injected into the organic film from the anode and cathode electrodes, respectively. When excitons which are generated from recombining the injected holes and electrons return from an excited state to a ground state, light emission occurs.

The capacitor 80 includes first and second storage electrodes 158 and 178 with an insulation film 140 (illustrated in FIG. 2) interposed therebetween.

Each of the first and second TFTs 10 and 20 includes a gate electrode 152 and 155, a source electrode 173 and 176, a drain electrode 174 and 177, and a semiconductor film 131 and 132. It will be appreciated that various configurations of TFTs are adapted for the first and second TFTs 10, 20.

The first TFT 10 is used as a switching element for selecting a pixel for light emission. The first gate electrode 152 of the first TFT 10 is electrically connected to the gate line 151. The first source electrode 173 is connected to the data line 171. The first drain electrode 176 of the first TFT 10 is connected to the first storage electrode 158 of the capacitor 80.

The second TFT **20** is configured to apply a driving power source to a first pixel electrode **710** for light emission of an organic film **720** (illustrated in FIG. 2) of the selected OLED **70**. Here, the first pixel electrode **710** can serve as an anode of the OLED **70**. In other embodiments, the first pixel electrode **710** may be used as a cathode of the OLED **70** depending on the method of driving the organic light emitting display device **901**. The second gate electrode **155** of the second TFT **20** is connected to the first storage electrode **158** of the capacitor **80**. The second source electrode **176** is connected to the common power source line **172**.

A planarization film **180** (illustrated in FIG. 2) is formed over the substrate, covering the TFTs **10**, **20**. The pixel electrode **710** of the OLED **70** is formed over the planarization film **180**. In addition, the second drain electrode **177** of the second TFT **20** is connected to the first pixel electrode **710** of the OLED **70** through a contact hole **181** in the planarization film **180**.

In the illustrated embodiment, the first TFT **10** is driven by a gate voltage which is applied to the gate line **151** to transfer a data voltage which is applied to the data line **171** to the second TFT **20**. A voltage corresponding to a difference between the common voltage which is applied to the second TFT **20** from the common power source line **172** and the data voltage which is transferred from the first TFT **10** is stored in the capacitor **80**. A current corresponding to the voltage stored in the capacitor **80** flows into the OLED **70** through the second TFT **20**, so that the OLED **70** emits light.

In addition, the organic light emitting display device **901** further includes a pixel defining layer **190** (illustrated in FIG. 2) formed over the planarization film **180**. The pixel defining layer **190** has an opening and partitions pixels.

In the illustrated embodiment, one side edge of the first pixel electrode **710** in a pixel region overlaps with the data line **171** crossing the pixel region. The side edge of the first pixel electrode **170** which overlaps with the data line **171** crosses the data line **171**, so that an end of the side edge also overlaps with the common power source line **172** of an adjacent pixel region.

In addition, the other side edge of the first pixel electrode **710** overlaps with the common power source line **172** crossing the pixel region. Here, the side edges of the first pixel electrode **710** are positioned on opposite sides of the pixel region.

In addition, the first pixel electrode **710** overlaps with the first and second TFTs **10** and **20**. In other words, the first pixel electrode **710** covers the first and second TFTs **10** and **20** when viewed from above the first pixel electrode **710**. Here, the first pixel electrode **710** is formed of a reflective conductive material through which substantially no light can pass.

The aforementioned structure prevents light generated from the OLED **70** from reaching the channel regions of the TFTs **10** and **20**. In other words, the first pixel electrode **710** of the OLED **70** covers the TFTs **10** and **20**, and extends to over the data line **171** and the common power source line **172** on boundaries of the pixel region. Accordingly, the first pixel electrode **710** blocks the light generated from the OLED **70** from reaching the channel regions of the TFTs **10** and **20**.

A structure of an organic light emitting display device **901** according to a first embodiment will now be described in detail with reference to FIG. 2. FIG. 2 illustrates a second TFT **20**, an OLED **70**, and a capacitor **80** of the organic light emitting display device.

The structure of a TFT will now be described, referring to the second TFT **20**. Since the structure of the first TFT **10** is the same as that of the second TFT **20**, detailed description on the first TFT **10** will be omitted. In FIG. 2, a substrate member

110 may be formed of an insulation substrate or a metal substrate. The insulation substrate may be formed of glass, quartz, ceramic, plastic, or the like. The metal substrate may be formed of stainless steel.

A buffer layer **120** may be formed on the substrate member **110**. The buffer layer **120** prevents penetration of impurities while planarizing the upper surface of the substrate member **110**. The buffer layer **120** may be formed of any material suitable for the above functions. In certain embodiments, the buffer layer **120** may be omitted depending on the type of the substrate member **110** and manufacturing conditions.

A semiconductor layer **132** may be formed on the buffer layer **120**. The semiconductor layer **132** may be formed of a polycrystalline silicon film. Here, the semiconductor layer **132** may be formed by coating amorphous silicon, and patterning and crystallizing the coated amorphous silicon. The semiconductor layer **132** includes a channel region **135**, a source region **136**, and a drain region **137**. The source and drain regions **136**, **137** may be formed by p+ doping both sides of the channel region **135**. The doping ion material may be a p-type impurity such as boron (B). B₂H₆ may be used as a doping ion material. The impurity can vary depending on the type of the TFT.

A gate insulation substrate **140** which is made of silicon oxide or silicon nitride is formed on the semiconductor layer **132**. A gate wiring including the gate electrode **155** is formed on the gate insulation substrate **140**. The gate wiring includes a gate line **151** (illustrated in FIG. 1), a first storage electrode **158** (illustrated in FIG. 1) and other wirings, although not illustrated in FIG. 2. The gate electrode **155** overlaps with at least a part of the semiconductor layer **132**, more particularly, the channel region **135**.

Although not illustrated in FIG. 2, the gate wiring may have multi-layers. For example, aluminum or aluminum alloy may be used as a lower layer. Molybdenum-tungsten or molybdenum-tungsten nitride may be used as an upper layer. Aluminum or aluminum alloy which has a low resistivity is used as the lower layer to prevent a signal resistance due to wiring resistance. Molybdenum-tungsten or molybdenum-tungsten nitride has high corrosion resistance to chemicals. These can be used for the upper layer in order to reinforce weak portions formed of aluminum or aluminum alloy. Aluminum or aluminum alloy has a low corrosion resistance to chemicals and is easily oxidized to cause disconnection. Recently, molybdenum, aluminum, titanium, tungsten, and the like have been spotlighted as wiring materials.

An interlayer insulation film **160** which covers the gate electrode **155** is formed on the gate insulation film **140**. The gate insulation film **140** and the interlayer insulation film **160** have contact holes **166** and **167** through which the source region **136** and drain region **137** of the semiconductor layer **132** are exposed. Here, a contact hole through which the source region **136** is exposed is referred to as a first contact hole **166**. A contact hole through which the drain region **137** is exposed is referred to as a second contact hole **167**.

A data wiring including the source and drain electrodes **176** and **177** is formed on the interlayer insulation film **160**. In addition, the data wiring may include a data line **171** (illustrated in FIG. 1), a common power source line **172** (illustrated in FIG. 1), a second storage electrode **178** (illustrated in FIG. 1) and other wirings, although not illustrated in FIG. 2. The source and drain electrodes **176** and **177** are connected to the source and drain regions **136** and **137** of the semiconductor layer **132** through the contact holes **166** and **167**, respectively. In certain embodiments, the data wiring may have a multi-layered structure.

However, the structures of the gate and data wirings are not limited to those described above. Accordingly, the structures of the gate and data wirings may vary, depending on structures of the first and second TFTs **10** and **20** and other wirings. In other words, the gate line, data line, common power source line, and other elements may be formed on a layer which is different from the layer in the embodiment. The semiconductor layer **132**, the gate electrode **155**, the source electrode **176**, and the drain electrode **177** which are formed as described above form the second TFT **20**.

The planarization film **180** which covers the data wirings **176** and **177** is formed on the interlayer insulation film **160**. The planarization film **180** provides a planar top surface, covering underlying structure and layers. The film **180** may also serve to increase the light emission efficiency of the OLED **70** which is to be formed on the film **180**. In addition, the planarization film **180** has a contact hole **181** which exposes a portion of the drain electrode **177**. Hereinafter, the contact hole **181** may be referred to as a third contact hole.

The planarization film **180** may be formed of any suitable material having superior characteristics of planarization. The planarization film **180** allows the organic film **720** to have a uniform thickness over the planarization film **180**. As a result, the organic film **720** may have uniform brightness, thereby increasing its light emitting efficiency. In addition, a defect such as a break and short-circuit between several conductive layers to be formed on the planarization film **180** can be prevented.

A first pixel electrode **710** of the OLED **70** may be formed on the planarization film **180**. The first pixel electrode **710** may be connected to the drain electrode **177** through the third contact hole **181** of the planarization film **180**. A pixel defining layer **190** which has a plurality of openings and defines pixels is formed on the planarization film **180** and a portion of the first pixel electrode **710**. Here, at least a portion of the first pixel electrode is exposed through the opening of the pixel defining layer **190**.

In the opening of the pixel defining layer **190**, an organic film **720** is formed on the first pixel electrode **710**. A second pixel electrode **730** is formed on the pixel defining layer **190** and the organic film **720**. Here, the second pixel electrode **730** becomes a cathode electrode of the OLED **70**. In other words, the OLED **70** includes the first pixel electrode **710**, the organic film **720**, and the second pixel electrode **730**.

The first pixel electrode **710** may be formed of reflective conductive materials. The second pixel electrode **730** may be formed of materials including transparent conductive materials. Examples of the transparent conductive materials include, but are not limited to, Indium Tin Oxide (ITO), Indium Zinc Oxide (IZO), ZnO, and In₂O₃ (Indium Oxide).

The organic film **720** may be formed of a low molecular weight organic compound or a polymeric compound. The organic film **720** may have multi-layers including a light emitting layer and at least one of a hole-injection layer (HIL), a hole-transporting layer (HTL), an electron-transporting layer (ETL), and an electron-injection layer (EIL). In certain embodiments, the HIL is formed on the first pixel electrode **710**. The HTL, the light emitting layer, the ETL, and the EIL may be sequentially stacked over the HIL.

A sealing member may be further formed on the second pixel electrode **730**, although not illustrated in FIG. 2.

An organic light emitting display device **902** according to a second embodiment will now be described with reference to FIG. 3. One side edge of the first pixel electrode **710** of a pixel region overlaps with the data line **171** crossing the pixel region, as illustrated in FIG. 3. The side edge of the first pixel electrode **170** which overlaps with the data line **171** may cross

the data line **171**. An end of the side edge may overlap with the data line although not illustrated in FIG. 2. In other words, one side edge of the first pixel electrode **710** does not overlap with the common power source line **172** of an adjacent pixel region.

In addition, the other side edge of the first pixel electrode **710** overlaps with the common power source line **172**. Here, the edges of the one side and the other side of first pixel electrode **710** are positioned on opposite sides of the pixel region.

The aforementioned structure prevents light generated from the OLED **70** from reaching the channel regions of the TFTs **10** and **20**. In other words, the first pixel electrode **710** of the OLED **70** is formed to cover the TFTs **10** and **20** while overlapping with the data line **171** and the common power source line **172** on a boundary of the pixel region. Accordingly, the first pixel electrode **710** blocks the light from reaching the channel regions of the TFTs **10** and **20**.

As described above, an organic light emitting display device according to an embodiment blocks light from reaching the channel regions of TFTs, thereby preventing a photo leakage current. This configuration prevents deterioration of driving characteristics of the TFTs. In other words, the first pixel electrode of the OLED is formed to cover the TFTs while overlapping with the data line and the common power source line on a boundary of the pixel region. Accordingly, the first pixel electrode can block the light generated by the OLED from reaching the channel regions of the TFTs due to reflection.

While the instant disclosure has been described in connection with exemplary embodiments, it is to be understood that the disclosure is not limited to the disclosed embodiments, but, on the contrary, is intended to cover various modifications and equivalent arrangements included within the spirit and scope of the appended claims.

What is claimed is:

1. An organic light emitting display device, comprising: an array of pixels formed over a substrate, each of the pixels comprising an organic light emitting diode (OLED), the OLED comprising a first pixel electrode, a second pixel electrode overlying the first pixel electrode, and an organic light emitting layer interposed between the first and second pixel electrodes, the first pixel electrode comprising a layer formed of a substantially opaque material;

- at least one thin film transistor (TFT) interposed between the substrate and one of the pixels;

- a data line connected to the TFT; and

- first and second common power source lines, formed over the substrate and extending adjacent to and substantially parallel to the data line,

- wherein the first pixel electrode of the one pixel extends across at least the entire width of the data line, partially overlaps the first and second common power source lines, and is configured to substantially block light emitting from the organic light emitting layer from reaching the thin film transistor.

2. The device of claim 1, wherein the first pixel electrode is configured to sufficiently block the light from reaching the TFT such that substantially no photo leakage current occurs at the TFT.

3. The device of claim 1, wherein the first pixel electrode at least partially overlies the TFT.

4. The device of claim 3, wherein the TFT comprises a semiconductor layer including a channel region, and wherein the first pixel electrode overlies substantially the entire channel region.

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5. The device of claim 3, wherein the first pixel electrode overlies substantially the entire portion of the TFT.

6. The device of claim 1, further comprising a second thin film transistor (TFT), wherein the common power source line is electrically connected to the second TFT.

7. The device of claim 1, wherein the TFT is positioned under the first pixel electrode, and wherein the first pixel electrode overlies substantially the entire TFT.

8. The device of claim 1, wherein the substantially opaque material comprises silver (Ag) or a silver alloy.

9. The device of claim 1, wherein the first pixel electrode further comprises a layer formed of a substantially transparent material.

10. The device of claim 9, wherein the substantially transparent material comprises indium tin oxide (ITO).

11. The device of claim 10, wherein the first electrode has an ITO/Ag/ITO layer structure.

12. An organic light emitting display device comprising:
a plurality of data lines formed over a substrate, the data lines extending substantially parallel to one another; and

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a plurality of power lines formed over the substrate, the power lines extending substantially parallel to one another and to the data lines, the power lines alternating with the data lines; and

an array of organic light emitting diodes (OLEDs), each of the OLEDs comprising a first pixel electrode, a second pixel electrode overlying the first pixel electrode, and an organic light emitting layer interposed between the first and second pixel electrodes, the first pixel electrode comprising a layer formed of a substantially opaque material,

wherein the first pixel electrode of each OLED extends across at least the entire width of one of the plurality of data lines, and wherein the first pixel electrode extends so as to partially overlap two of the power lines.

13. The device of claim 12, further comprising at least one thin film transistor formed over the substrate and under the at least one first pixel electrode.

14. The device of claim 13, wherein the at least one first pixel electrode is configured to substantially block light emitting from the organic light emitting layer from reaching the thin film transistor.

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专利名称(译)	具有不透明电极的有机发光显示装置		
公开(公告)号	US7982386	公开(公告)日	2011-07-19
申请号	US11/728628	申请日	2007-03-26
[标]申请(专利权)人(译)	白智英YEON 李准WOO		
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摘要(译)

公开了一种有机发光显示装置。有机发光显示装置的一个实施例包括：基板构件，其中布置有多个像素区域；以及多个薄膜晶体管，分别形成在像素区域上。该装置还包括沿着每个像素区域的一侧边缘布置的数据线和沿着多个像素区域中的每个像素区域的另一侧边缘布置并且基本上平行于数据线的公共电源线。该器件还包括第一像素电极，该第一像素电极电连接到多个薄膜晶体管中的一个并形成在像素区域的每个区域中。该器件还包括形成在第一像素电极上的有机膜，以及形成在有机膜上的第二像素电极。第一像素电极的靠近数据线的一侧边缘与数据线重叠。

